L Number	Hits	Search Text	DB	Time stamp
1	0	(mosfet adj model).ti.	USPAT	2004/07/09 13:03
2	1	(mosfet and model).ti.	USPAT	2004/07/09 13:04
3	10	BSIM3V3	USPAT	2004/07/09 13:04
4	371	diode near model	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 13:05
5	72	(diode near model) and mosfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 13:05
6	60	((diode near model) and mosfet) and parallel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 13:49
7	277	(703/15).CCLS.	USPAT	2004/07/09 13:49
8	2	((703/15).CCLS.) and (mosfet adj model)	USPAT	2004/07/09 13:49

Welcome to IEEE Xplore

- Home
- What Can I Access?
- Log-out

Tables of Contents

- Journals & Magazines
- Conference Proceedings
- Standards

Search

- By Author
- Basic
- Advanced

Member Services

- Join IEEE
- Establish IEEE Web Account
- Access the IEEE Member Digital Library

IEEE Enterprise

- Access the IEEE Enterprise File Cabinet

Print Format

Your search matched **46** of **1049776** documents.
A maximum of **500** results are displayed, **15** to a page, sorted by **Relevance** in **Descending** order.

Refine This Search:
You may refine your search by editing the current search expression or entering a new one in the text box.

mosfet <and> direct <and> tunneling <and> current <ar Search

Check to search within this result set

Results Key:
JNL = Journal or Magazine **CNF** = Conference **STD** = Standard

---

1 **Edge hole direct tunneling leakage in ultrathin gate oxide p-channel MOSFETs**
Kuo-Nan Yang; Huan-Tsung Huang; Ming-Jer Chen; Yeou-Ming Lin; Mo-Chiun Yu; Jang, S.S.A.; Yu, D.C.H.; Mong-Song Liang;
Electron Devices, IEEE Transactions on , Volume: 48 , Issue: 12 , Dec. 2001
Pages:2790 - 2795

[Abstract] [PDF Full-Text (152 KB)] **IEEE JNL**

---

2 **MOSFET gate leakage modeling and selection guide for alternative gate dielectrics based on leakage considerations**
Yee-Chia Yeo; Tsu-Jae King; Chenming Hu;
Electron Devices, IEEE Transactions on , Volume: 50 , Issue: 4 , April 2003
Pages:1027 - 1035

[Abstract] [PDF Full-Text (756 KB)] **IEEE JNL**

---

3 **Scaling effects on gate leakage current**
Watanabe, H.; Matsuzawa, K.; Takagi, S.;
Electron Devices, IEEE Transactions on , Volume: 50 , Issue: 8 , Aug. 2003
Pages:1779 - 1784

[Abstract] [PDF Full-Text (471 KB)] **IEEE JNL**

---

4 **Modeling of direct tunneling gate current in ultra-thin gate oxide MOSFETs: a comparison between simulators**
Cassan, E.; Galdin, S.; Dollfus, P.; Hesto, P.;
Simulation of Semiconductor Processes and Devices, 1999. SISPAD '99. 1999 International Conference on , 6-8 Sept. 1999
Pages:115 - 118

[Abstract] [PDF Full-Text (272 KB)] **IEEE CNF**

---

5 **Effects of neglecting carrier tunneling on electrostatic potential in calculating direct tunneling gate current in deep submicron MOSFETs**
Hakim, M.M.A.; Haque, A.;

Electron Devices, IEEE Transactions on , Volume: 49 , Issue: 9 , Sept. 2002
Pages:1669 - 1671

[Abstract] [PDF Full-Text (230 KB)] **IEEE JNL**

---

6 **Direct tunneling gate leakage current in transistors with ultrathin silicon nitride gate dielectric**
Yee Chia Yeo; Qiang Lu; Wen Chin Lee; Tsu-Jae King; Chenming Hu; Xiewen Wang; Xin Guo; Ma, T.P.;
Electron Device Letters, IEEE , Volume: 21 , Issue: 11 , Nov. 2000
Pages:540 - 542

[Abstract] [PDF Full-Text (104 KB)] **IEEE JNL**

---

7 **A comparative study of gate direct tunneling and drain leakage currents in n-MOSFET's with sub-2 nm gate oxides**
Yang, N.; Henson, W.K.; Wortman, J.J.;
Electron Devices, IEEE Transactions on , Volume: 47 , Issue: 8 , Aug. 2000
Pages:1636 - 1644

[Abstract] [PDF Full-Text (236 KB)] **IEEE JNL**

---

8 **The influence of localized states on gate tunnel currents-modeling and simulation**
Wettstein, A.; Schenk, A.; Scholze, A.; Fichtner, W.;
Simulation of Semiconductor Processes and Devices, 1997. SISPAD '97., 1997 International Conference on , 8-10 Sept. 1997
Pages:101 - 104

[Abstract] [PDF Full-Text (272 KB)] **IEEE CNF**

---

9 **Impact of high-/spl kappa/ dielectrics on undoped double-gate MOSFET scaling**
Qiang Chen; Lihui Wang; Meindl, J.D.;
SOI Conference, IEEE International 2002 , 7-10 Oct. 2002
Pages:115 - 116

[Abstract] [PDF Full-Text (245 KB)] **IEEE CNF**

---

10 **Modeling the limits of gate oxide scaling with a Schrodinger-based method of direct tunneling gate currents of nanoscale MOSFETs**
Chung-Kuang Huang; Goldsman, N.;
Nanotechnology, 2001. IEEE-NANO 2001. Proceedings of the 2001 1st IEEE Conference on , 28-30 Oct. 2001
Pages:335 - 340

[Abstract] [PDF Full-Text (449 KB)] **IEEE CNF**

---

11 **Simulation of direct tunneling through stacked gate dielectrics by a fully integrated 1D-Schrodinger-Poisson solver**
Wettstein, A.; Schenk, A.; Fichtner, W.;
Simulation of Semiconductor Processes and Devices, 1999. SISPAD '99. 1999 International Conference on , 6-8 Sept. 1999
Pages:243 - 246

[Abstract] [PDF Full-Text (260 KB)] **IEEE CNF**

---

12 **Noise modeling for RF CMOS circuit simulation**
Scholten, A.J.; Tiemeijer, L.F.; van Langevelde, R.; Havens, R.J.; Zegers-van

Duijnhoven, A.T.A.; Venezia, V.C.;
Electron Devices, IEEE Transactions on , Volume: 50 , Issue: 3 , March 2003
Pages:618 - 632

[Abstract] [PDF Full-Text (809 KB)] **IEEE JNL**

---

13 **Direct observation of secondary ionization current in n-channel MOSFETs**
Mihnea, A.; Rudeck, P.J.; Chun Chen; Prall, K.D.; Ghodsi, R.;
Electron Devices, IEEE Transactions on , Volume: 49 , Issue: 12 , Dec. 2002
Pages:2301 - 2307

[Abstract] [PDF Full-Text (379 KB)] **IEEE JNL**

---

14 **Voltage- and temperature-dependent gate capacitance and current model: application to ZrO/sub 2/ n-channel MOS capacitor**
Yang-Yu Fan; Nieh, R.E.; Lee, J.C.; Lucovsky, G.; Brown, G.A.; Register, L.F.; Banerjee, S.K.;
Electron Devices, IEEE Transactions on , Volume: 49 , Issue: 11 , Nov. 2002
Pages:1969 - 1978

[Abstract] [PDF Full-Text (509 KB)] **IEEE JNL**

---

15 **Model and analysis of gate leakage current in ultrathin nitrided oxide MOSFETs**
Jonghwan Lee; Bosman, G.; Green, K.R.; Ladwig, D.;
Electron Devices, IEEE Transactions on , Volume: 49 , Issue: 7 , July 2002
Pages:1232 - 1241

[Abstract] [PDF Full-Text (406 KB)] **IEEE JNL**

---

1 2 3 4 Next

Your search matched **5** of **1049776** documents.
A maximum of **500** results are displayed, **15** to a page, sorted by **Relevance** in **Descending** order.

Refine This Search:
You may refine your search by editing the current search expression or entering a new one in the text box.

(resonant <and> tunneling <and> diodes:models) <in> Search

Check to search within this result set

Results Key:
JNL = Journal or Magazine **CNF** = Conference **STD** = Standard

---

1 **An improved multipeak resonant tunneling diode model for nine-state resonant tunneling diode memory circuit simulation**
Chih Yuan Huang; Morris, J.E.; Yan Kuin Su;
Electron Devices, IEEE Transactions on , Volume: 42 , Issue: 9 , Sept. 1995
Pages:1705 - 1707

[Abstract] [PDF Full-Text (256 KB)] **IEEE JNL**

---

2 **Resonant tunneling diodes: models and properties**
Jian Ping Sun; Haddad, G.I.; Mazumder, P.; Schulman, J.N.;
Proceedings of the IEEE , Volume: 86 , Issue: 4 , April 1998
Pages:641 - 660

[Abstract] [PDF Full-Text (356 KB)] **IEEE JNL**

---

3 **SPICE implementation of double barrier resonant tunnel diode model**
Neculoiu, D.; Tebeanu, T.;
Semiconductor Conference, 1996., International , Volume: 1 , 9-12 Oct. 1996
Pages:181 - 184 vol.1

[Abstract] [PDF Full-Text (276 KB)] **IEEE CNF**

---

4 **Combined self-consistent resonant-tunneling diode model**
Abramov, I.I.; Goncharenko, I.A.;
Microwave and Telecommunication Technology, 2001. CriMiCo 2001. 11th International Conference on , 2001
Pages:443 - 444

[Abstract] [PDF Full-Text (295 KB)] **IEEE CNF**

---

5 **Large-signal resonant tunneling diode model for SPICE3 simulation**
Kuo, T.-H.; Lin, H.C.; Anandakrishnan, U.; Potter, R.C.; Shupe, D.;
Electron Devices Meeting, 1989. Technical Digest., International , 3-6 Dec. 1989
Pages:567 - 570

[Abstract] [PDF Full-Text (208 KB)] **IEEE CNF**